MSKSEMI















ESD

TVS

TSS

MOV

GDT

PLED

Broduct data sheet





1. BASE

2. EMITTER **SOT - 23**

3. COLLECTOR

TRANSISTOR (NPN)

FEATURES

- High Collector Current.
- Complementary to S9012-MS
- Excellent h_{FE} Linearity.

MARKING: J3

MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

| Symbol | Parameter | Value | Unit |
|----------------------------------|---|----------|------|
| V _{CBO} | Collector-Base Voltage | 40 | V |
| V _{CEO} | Collector-Emitter Voltage | 25 | V |
| V _{EBO} | Emitter-Base Voltage | 5 | V |
| Ic | Collector Current | 500 | mA |
| Pc | Collector Power Dissipation | 300 | mW |
| R _{OJA} | Thermal Resistance From Junction To Ambient | 416 | °C/W |
| T _J ,T _{stg} | Operation Junction and Storage Temperature Range | -55∼+150 | ℃ |

ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

| Parameter | Symbol | Test conditions | Min | Тур | Max | Unit |
|--------------------------------------|----------------------|---|-----|-----|-----|------|
| Collector-base breakdown voltage | V _{(BR)CBO} | I _C =0.1mA, I _E =0 | 40 | | | V |
| Collector-emitter breakdown voltage | V _{(BR)CEO} | I _C =1mA, I _B =0 | 25 | | | V |
| Emitter-base breakdown voltage | V _{(BR)EBO} | I _E =0.1mA, I _C =0 | 5 | | | V |
| Collector cut-off current | I _{CBO} | V _{CB} =40V, I _E =0 | | | 0.1 | uA |
| Collector cut-off current | I _{CEO} | V _{CE} =20V, I _B =0 | | | 0.1 | uA |
| Emitter cut-off current | I _{EBO} | V _{EB} =5V, I _C =0 | | | 0.1 | uA |
| DO | h _{FE(1)} | V _{CE} =1V, I _C =50mA | 120 | | 400 | |
| DC current gain | h _{FE(2)} | V _{CE} =1V, I _C =500mA | 40 | | | |
| Collector-emitter saturation voltage | V _{CE(sat)} | I _C =500mA, I _B =50mA | | | 0.6 | V |
| Base-emitter saturation voltage | $V_{BE(sat)}$ | I _C =500mA, I _B =50mA | | | 1.2 | V |
| Base-emitter voltage | V_{BE} | V _{CB} =1V,I _C =10mA, | | | 0.7 | V |
| Transition frequency | f _T | V _{CE} =6V,I _C =20mA, f=30MHz | 150 | | | MHz |
| Collector output capacitance | C _{ob} | V _{CB} =6V, I _E =0, f=1MHz | | | 8 | pF |

CLASSIFICATION OF h_{FE(1)}

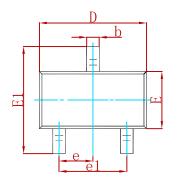
| RANK | L | Н | J |
|----------------------|---|---------|---------|
| RANGE 120-200 | | 200-350 | 300-400 |

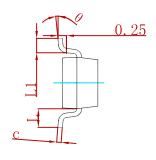


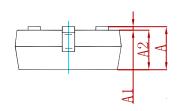




PACKAGE MECHANICAL DATA

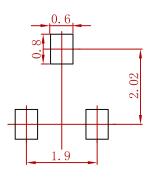






| Symbol | Dimensions | In Millimeters | Dimensions In Inches | | |
|--------|------------|----------------|----------------------|-------|--|
| Зупроі | Min | Max | Min | Max | |
| Α | 0.900 | 1.150 | 0.035 | 0.045 | |
| A1 | 0.000 | 0.100 | 0.000 | 0.004 | |
| A2 | 0.900 | 1.050 | 0.035 | 0.041 | |
| b | 0.300 | 0.500 | 0.012 | 0.020 | |
| С | 0.080 | 0.150 | 0.003 | 0.006 | |
| D | 2.800 | 3.000 | 0.110 | 0.118 | |
| Е | 1.200 | 1.400 | 0.047 | 0.055 | |
| E1 | 2.250 | 2.550 | 0.089 | 0.100 | |
| е | 0.950 TYP | | 0.037 TYP | | |
| e1 | 1.800 | 2.000 | 0.071 | 0.079 | |
| L | 0.550 REF | | 0.022 REF | | |
| L1 | 0.300 | 0.500 | 0.012 | 0.020 | |
| θ | 0° | 8° | 0° | 8° | |

Suggested Pad Layout



- 1.Controlling dimension:in millimeters.2.General tolerance:± 0.05mm.3.The pad layout is for reference purposes only.

REEL SPECIFICATION

| P/N | PKG | QTY |
|----------|--------|------|
| S9013-MS | SOT-23 | 3000 |



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